

Geok Ing Ng

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207
papers

2,765
citations

26
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41
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240
ext. papers

3,237
ext. citations

2.7
avg, IF

4.84
L-index

#	Paper	IF	Citations
207	Flexible Ionic-Electronic Hybrid Oxide Synaptic TFTs with Programmable Dynamic Plasticity for Brain-Inspired Neuromorphic Computing. <i>Small</i> , 2017 , 13, 1701193	11	110
206	AlGa _N /Ga _N two-dimensional-electron gas heterostructures on 200 mm diameter Si(111). <i>Applied Physics Letters</i> , 2012 , 101, 082110	3.4	85
205	Improved two-dimensional electron gas transport characteristics in AlGa _N /Ga _N metal-insulator-semiconductor high electron mobility transistor with atomic layer-deposited Al ₂ O ₃ as gate insulator. <i>Applied Physics Letters</i> , 2009 , 95, 223501	3.4	85
204	Reduced surface leakage current and trapping effects in AlGa _N /Ga _N high electron mobility transistors on silicon with SiN/Al ₂ O ₃ passivation. <i>Applied Physics Letters</i> , 2011 , 98, 113506	3.4	81
203	Reactive sputter deposition and characterization of tantalum nitride thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 57, 224-227	3.1	72
202	0.10 THz graded InGaAs channel InP HEMT with 305 GHz f _T and 340 GHz f _{max} . <i>IEEE Electron Device Letters</i> , 1994 , 15, 477-479	4.4	65
201	Low- and high-field transport properties of pseudomorphic In _x Ga _{1-x} As/In _{0.52} Al _{0.48} As (0.53x0.65) modulation-doped heterostructures. <i>Journal of Applied Physics</i> , 1988 , 64, 1945-1949	2.5	59
200	Atomic layer deposition of ZrO ₂ as gate dielectrics for AlGa _N /Ga _N metal-insulator-semiconductor high electron mobility transistors on silicon. <i>Applied Physics Letters</i> , 2013 , 103, 142109	3.4	54
199	Temperature dependence of Ohmic contact characteristics in AlGa _N /Ga _N high electron mobility transistors from 80 to 200 °C. <i>Applied Physics Letters</i> , 2009 , 94, 142105	3.4	53
198	Low-Temperature Chemical Transformations for High-Performance Solution-Processed Oxide Transistors. <i>Chemistry of Materials</i> , 2016 , 28, 8305-8313	9.6	51
197	Temperature-dependent forward gate current transport in atomic-layer-deposited Al ₂ O ₃ /AlGa _N /Ga _N metal-insulator-semiconductor high electron mobility transistor. <i>Applied Physics Letters</i> , 2011 , 98, 163501	3.4	49
196	Temperature dependent microwave performance of AlGa _N /Ga _N high-electron-mobility transistors on high-resistivity silicon substrate. <i>Thin Solid Films</i> , 2007 , 515, 4517-4521	2.2	46
195	. <i>IEEE Transactions on Electron Devices</i> , 1989 , 36, 2249-2259	2.9	45
194	High Microwave-Noise Performance of AlGa _N /Ga _N MISHEMTs on Silicon With Al ₂ O ₃ Gate Insulator Grown by ALD. <i>IEEE Electron Device Letters</i> , 2010 , 31, 96-98	4.4	44
193	Improved Linearity for Low-Noise Applications in 0.25- μm Ga _N MISHEMTs Using ALD Al ₂ O ₃ as Gate Dielectric. <i>IEEE Electron Device Letters</i> , 2010 , 31, 803-805	4.4	43
192	Improved Power Device Figure-of-Merit ($4.0 \times 10^8 \text{ V}^2 \text{ s}^{-1} \text{ cm}^{-2}$) in AlGa _N /Ga _N High-Electron-Mobility Transistors on High-Resistivity 4-in. Si. <i>Applied Physics Express</i> , 2011 , 4, 084101	2.4	43
191	Enhanced Breakdown Voltage With High Johnson's Figure-of-Merit in 0.3- μm T-gate AlGa _N /Ga _N HEMTs on Silicon by NH ₄ S _x Treatment. <i>IEEE Electron Device Letters</i> , 2013 , 34, 1364-1366	4.4	42

190	Effect of gate-source and gate-drain Si ₃ N ₄ passivation on current collapse in AlGaIn/GaN high-electron-mobility transistors on silicon. <i>Applied Physics Letters</i> , 2007 , 90, 173504	3-4	41
189	Demonstration of Submicron-Gate AlGaIn/GaN High-Electron-Mobility Transistors on Silicon with Complementary MetalOxideSemiconductor-Compatible Non-Gold Metal Stack. <i>Applied Physics Express</i> , 2013 , 6, 016501	2-4	39
188	Metamorphic InP/InGaAs double-heterojunction bipolar transistors on GaAs grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2000 , 77, 869-871	3-4	38
187	InAlN/GaN HEMTs on Si With High f_{T} of 250 GHz. <i>IEEE Electron Device Letters</i> , 2018 , 39, 75-78	4-4	36
186	. <i>IEEE Electron Device Letters</i> , 1988 , 9, 439-441	4-4	36
185	Direct Current and Microwave Characteristics of Sub-micron AlGaIn/GaN High-Electron-Mobility Transistors on 8-Inch Si(111) Substrate. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 111001	1-4	36
184	. <i>IEEE Transactions on Electron Devices</i> , 1988 , 35, 1223-1231	2-9	33
183	Electrothermal Large-Signal Model of III-V FETs Including Frequency Dispersion and Charge Conservation. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2009 , 57, 3106-3117	4-1	32
182	Band alignment between GaN and ZrO ₂ formed by atomic layer deposition. <i>Applied Physics Letters</i> , 2014 , 105, 022106	3-4	26
181	Direct Current and Microwave Characteristics of Sub-micron AlGaIn/GaN High-Electron-Mobility Transistors on 8-Inch Si(111) Substrate. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 111001	1-4	25
180	Demonstration of AlGaIn/GaN high-electron-mobility transistors on 100 mm diameter Si(111) by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2010 , 97, 232107	3-4	25
179	Low-frequency noise characteristics of lattice-matched ($x=0.53$) and strained ($x>0.53$) In/sub 0.52/Al/sub 0.48/As/InxGa/sub 1-xAs HEMT's. <i>IEEE Transactions on Electron Devices</i> , 1992 , 39, 523-532	2-9	25
178	High temperature power performance of AlGaIn/GaN high-electron-mobility transistors on high-resistivity silicon. <i>Applied Physics Letters</i> , 2007 , 91, 083516	3-4	24
177	Demonstration of aluminum-free metamorphic InP/In/sub 0.53/Ga/sub 0.47/As/InP double heterojunction bipolar transistors on GaAs substrates. <i>IEEE Electron Device Letters</i> , 2000 , 21, 427-429	4-4	23
176	Planar-Nanostrip-Channel InAlN/GaN HEMTs on Si With Improved g_{m} and f_{T} Linearity. <i>IEEE Electron Device Letters</i> , 2017 , 38, 619-622	4-4	22
175	. <i>IEEE Electron Device Letters</i> , 2014 , 35, 992-994	4-4	22
174	The relation of the performance characteristics of pseudomorphic In _{0.53+x} Ga _{0.47-x} As/In _{0.52} Al _{0.48} As (0.32) modulation-doped field-effect transistors to molecular-beam epitaxial growth modes. <i>Journal of Applied Physics</i> , 1990 , 68, 347-350	2-5	22
173	A Compact Model for Generic MIS-HEMTs Based on the Unified 2DEG Density Expression. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 314-323	2-9	21

172	Study of the consequence of excess indium in the active channel of InGaAs/InAlAs high electron mobility transistors on device properties. <i>Applied Physics Letters</i> , 1988 , 52, 728-730	3.4	21
171	Planar Nanostrip-Channel Al ₂ O ₃ /InAlN/GaN MISHEMTs on Si With Improved Linearity. <i>IEEE Electron Device Letters</i> , 2018 , 39, 947-950	4.4	20
170	Influence of Ammonia in the Deposition Process of SiN on the Performance of SiN/AlGaIn/GaN Metal-Insulator-Semiconductor High-Electron-Mobility Transistors on 4-in. Si(111). <i>Applied Physics Express</i> , 2009 , 2, 031001	2.4	20
169	Low-Contact-Resistance Non-Gold Ta/Si/Ti/Al/Ni/Ta Ohmic Contacts on Undoped AlGaIn/GaN High-Electron-Mobility Transistors Grown on Silicon. <i>Applied Physics Express</i> , 2013 , 6, 116501	2.4	19
168	A nanoelectromechanical systems actuator driven and controlled by Q-factor attenuation of ring resonator. <i>Applied Physics Letters</i> , 2013 , 103, 181105	3.4	19
167	Characterization of linearly graded metamorphic InGaP buffer layers on GaAs using high-resolution X-ray diffraction. <i>Thin Solid Films</i> , 2001 , 391, 36-41	2.2	19
166	. <i>IEEE Transactions on Electron Devices</i> , 1991 , 38, 862-870	2.9	19
165	Design of Coupled Three-Line Impedance Transformers. <i>IEEE Microwave and Wireless Components Letters</i> , 2014 , 24, 84-86	2.6	18
164	Improved recess-ohmics in AlGaIn/GaN high-electron-mobility transistors with AlN spacer layer on silicon substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 2412-2414		18
163	. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 1993 , 41, 1-8	4.1	18
162	Reduction of current collapse in AlGaIn/GaN MISHEMT with bilayer SiN/Al ₂ O ₃ dielectric gate stack. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1421-1425		17
161	Suppression of I-V kink in doped channel InAlAs/InGaAs/InP heterojunction field-effect transistor (HFET) using silicon nitride passivation. <i>Electronics Letters</i> , 1996 , 32, 2026	1.1	17
160	Avalanche multiplication in InP/InGaAs double heterojunction bipolar transistors with composite collectors. <i>IEEE Transactions on Electron Devices</i> , 2000 , 47, 1125-1133	2.9	17
159	Electrical and optical properties of Si-doped InP grown by solid source molecular beam epitaxy using a valved phosphorus cracker cell. <i>Journal of Applied Physics</i> , 2000 , 87, 7988-7993	2.5	17
158	W-band monolithic oscillator using InAlAs/InGaAs HEMT. <i>Electronics Letters</i> , 1990 , 26, 1425	1.1	17
157	Investigation of gate leakage current mechanism in AlGaIn/GaN high-electron-mobility transistors with sputtered TiN. <i>Journal of Applied Physics</i> , 2017 , 121, 044504	2.5	16
156	High Johnson figure of merit (8.32 THz/V) in 0.15- μ m conventional T-gate AlGaIn/GaN HEMTs on silicon. <i>Applied Physics Express</i> , 2014 , 7, 044102	2.4	16
155	Conversion between EIT and Fano spectra in a microring-Bragg grating coupled-resonator system. <i>Applied Physics Letters</i> , 2017 , 111, 081105	3.4	16

154	Improved Device Performance by Post-Oxide Annealing in Atomic-Layer-Deposited Al ₂ O ₃ /AlGaN/GaN Metal Insulator Semiconductor High Electron Mobility Transistor on Si. <i>Applied Physics Express</i> , 2011 , 4, 104102	2.4	16
153	. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 1492-1497	2.9	16
152	Preparation and characterization of rf-sputtered SrTiO ₃ thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2000 , 18, 1638-1641	2.9	16
151	Fully passivated W-band InAlAs/InGaAs/InP monolithic low noise amplifiers. <i>IET Microwaves Antennas and Propagation</i> , 1996 , 143, 361		16
150	Electromagnetically induced transparency-like effect in microring-Bragg gratings based coupling resonant system. <i>Optics Express</i> , 2016 , 24, 25665-25675	3.3	16
149	A Comprehensive Compact Model for GaN HEMTs, Including Quasi-Steady-State and Transient Trap-Charge Effects. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1478-1485	2.9	16
148	Record-low contact resistance for InAlN/AlN/GaN high electron mobility transistors on Si with non-gold metal. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 04DF12	1.4	15
147	Demonstration of AlGaIn/GaN High-Electron-Mobility Transistors on 100-mm-Diameter Si(111) by Ammonia Molecular Beam Epitaxy. <i>Applied Physics Express</i> , 2012 , 5, 091003	2.4	15
146	Improved strained HEMT characteristics using double-heterojunction In _{0.35} /As/In _{0.52} /Al _{0.48} /As design. <i>IEEE Electron Device Letters</i> , 1989 , 10, 114-116	4.4	15
145	Thermally stable device isolation by inert gas heavy ion implantation in AlGaIn/GaN HEMTs on Si. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 042203	1.3	15
144	Modal gain characteristics of a 2 μm InGaSb/AlGaAsSb passively mode-locked quantum well laser. <i>Applied Physics Letters</i> , 2017 , 111, 251105	3.4	14
143	Analytical Modeling of High-Frequency Noise Including Temperature Effects in GaN HEMTs on High-Resistivity Si Substrates. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 1485-1491	2.9	14
142	Role of two-dimensional electron gas (2DEG) in AlGaIn/GaN high electron mobility transistor (HEMT) ON-state degradation. <i>Microelectronics Reliability</i> , 2016 , 64, 589-593	1.2	14
141	Deeply-scaled GaN-on-Si high electron mobility transistors with record cut-off frequency f _T of 310 GHz. <i>Applied Physics Express</i> , 2019 , 12, 126506	2.4	14
140	Electron velocity of 6 × 10 ⁷ cm/s at 300 K in stress engineered InAlN/GaN nano-channel high-electron-mobility transistors. <i>Applied Physics Letters</i> , 2015 , 106, 053502	3.4	13
139	Effect of OFF-state stress induced electric field on trapping in AlGaIn/GaN high electron mobility transistors on Si (111). <i>Applied Physics Letters</i> , 2015 , 106, 083508	3.4	12
138	Conduction mechanism of non-gold Ta/Si/Ti/Al/Ni/Ta ohmic contacts in AlGaIn/GaN high-electron-mobility transistors. <i>Applied Physics Express</i> , 2015 , 8, 041001	2.4	12
137	Influence of post-deposition annealing on interfacial properties between GaN and ZrO ₂ grown by atomic layer deposition. <i>Applied Physics Letters</i> , 2014 , 105, 152104	3.4	12

136	Low Specific On-Resistance AlGa _N /AlN/GaN High Electron Mobility Transistors on High Resistivity Silicon Substrate. <i>Electrochemical and Solid-State Letters</i> , 2010 , 13, H169		12
135	Improved Microwave Noise Performance by SiN Passivation in AlGa _N /Ga _N HEMTs on Si. <i>IEEE Microwave and Wireless Components Letters</i> , 2009 , 19, 383-385	2.6	12
134	Enhancement of both direct-current and microwave characteristics of AlGa _N /Ga _N high-electron-mobility transistors by furnace annealing. <i>Applied Physics Letters</i> , 2006 , 88, 023502	3.4	12
133	. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 2192-2197	2.9	12
132	Studies on the Degradation of InP/InGaAs/InP Double Heterojunction Bipolar Transistors Induced by Silicon Nitride Passivation. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, 1059-1061	1.4	12
131	A high-efficiency 94-GHz 0.15-W InGaAs/InAlAs/InP monolithic power HEMT amplifier 1996 , 6, 366-368		12
130	(Invited) SiGe and III-V Materials and Devices: New HEMT and LED Elements in 0.18-Micron CMOS Process and Design. <i>ECS Transactions</i> , 2016 , 75, 439-446	1	12
129	Growth and characterization of AlGa _N /Ga _N /AlGa _N double-heterojunction high-electron-mobility transistors on 100-mm Si(111) using ammonia-molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2015 , 117, 025301	2.5	11
128	Positive Bias-Induced V_{th} Instability in Graphene Field Effect Transistors. <i>IEEE Electron Device Letters</i> , 2012 , 33, 339-341	4.4	11
127	Analysis of dark-line defect growth suppression in In _x Ga _{1-x} As/GaAs strained heterostructures. <i>Journal of Applied Physics</i> , 1997 , 81, 3117-3123	2.5	11
126	Fabrication and characteristics of In _{0.48} Ga _{0.52} P/In _{0.20} Ga _{0.80} As/GaAs pseudomorphic high electron mobility transistor grown by solid-source molecular beam epitaxy. <i>Microelectronics Journal</i> , 1999 , 30, 23-28	1.8	11
125	CMOS-compatible GaN-on-Si HEMTs with cut-off frequency of 210 GHz and high Johnson figure-of-merit of 8.8 THz V. <i>Applied Physics Express</i> , 2020 , 13, 026503	2.4	11
124	Impact of post-deposition annealing on interfacial chemical bonding states between AlGa _N and ZrO ₂ grown by atomic layer deposition. <i>Applied Physics Letters</i> , 2015 , 106, 091603	3.4	10
123	Sheet carrier density enhancement by Si ₃ N ₄ passivation on nonpolar a-plane (1120) sapphire grown AlGa _N /Ga _N heterostructures. <i>Applied Physics Letters</i> , 2008 , 92, 092116	3.4	10
122	Current transient in polyimide-passivated InP/InGaAs heterojunction bipolar transistors: systematic experiments and physical model. <i>IEEE Transactions on Electron Devices</i> , 2000 , 47, 2261-2269	2.9	10
121	Dry via hole etching of GaAs using high-density Cl ₂ /Ar plasma. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 2509		10
120	Characterization of silicon-doped InP grown by solid-source molecular beam epitaxy using a valved phosphorus cracker cell. <i>Journal of Crystal Growth</i> , 1999 , 204, 275-281	1.6	10
119	A silicon-nanowire memory driven by optical gradient force induced bistability. <i>Applied Physics Letters</i> , 2015 , 107, 261111	3.4	9

118	High vertical breakdown strength in with low specific on-resistance AlGa _N /AlN/GaN HEMTs on silicon. <i>Physica Status Solidi - Rapid Research Letters</i> , 2011 , 5, 37-39	2.5	9
117	Temperature dependent microwave noise parameters and modeling of AlGa _N /Ga _N HEMTs on Si substrate 2009 ,		9
116	Metamorphic InP/InGaAs heterojunction bipolar transistors on GaAs substrate: DC and microwave performances. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 2671-2676	2.9	9
115	An ultra-low noise cryogenic Ka-Band InGaAs/InAlAs/InP HEMT front-end receiver 1994 , 4, 329-331		9
114	GaN drift-layer thickness effects in vertical Schottky barrier diodes on free-standing HVPE GaN substrates. <i>AIP Advances</i> , 2019 , 9, 045007	1.5	8
113	Mid-Infrared Sensor Based on a Suspended Microracetrack Resonator With Lateral Subwavelength-Grating Metamaterial Cladding. <i>IEEE Photonics Journal</i> , 2018 , 10, 1-8	1.8	8
112	AlGa _N /Ga _N high electron mobility transistors on Si with sputtered TiN gate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600555	1.6	8
111	Distribution of trap energy level in AlGa _N /Ga _N high-electron-mobility transistors on Si under ON-state stress. <i>Applied Physics Express</i> , 2015 , 8, 104101	2.4	8
110	Identification of room temperature photoluminescence in pseudomorphic modulation-doped AlGaAs/InGaAs/GaAs quantum wells. <i>Journal of Applied Physics</i> , 1997 , 82, 1345-1349	2.5	8
109	A novel technology to form self-aligned emitter ledge for heterojunction bipolar transistors. <i>IEEE Electron Device Letters</i> , 2003 , 24, 628-630	4.4	8
108	Investigation of the degradation of InGaAs/InP double HBTs under reverse base-collector bias stress. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 2647-2654	2.9	8
107	Metamorphic In _{0.52} Al _{0.48} As/In _{0.53} Ga _{0.47} As high electron mobility transistors on GaAs with In _x Ga _{1-x} P graded buffer. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001 , 19, 2119		8
106	Growth optimization of InGaP layers by solid source molecular beam epitaxy for the application of InGaP/In _{0.2} Ga _{0.8} As/GaAs high electron mobility transistor structures. <i>Journal of Crystal Growth</i> , 2000 , 216, 51-56	1.6	8
105	Graded-channel InGaAs/InAlAs/InP high electron mobility transistors. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1995 , 13, 774		8
104	. <i>IEEE Electron Device Letters</i> , 1991 , 12, 360-362	4.4	8
103	Investigation of regime switching from mode locking to Q-switching in a 2 μm InGaSb/AlGaAsSb quantum well laser. <i>Optics Express</i> , 2018 , 26, 8289-8295	3.3	7
102	Study of current collapse by quiescent-bias-stresses in rf-plasma assisted MBE grown AlGa _N /Ga _N high-electron-mobility transistors. <i>Solid-State Electronics</i> , 2010 , 54, 1430-1433	1.7	7
101	Characterization of beryllium doped Al _{0.33} Ga _{0.67} As layers grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1999 , 197, 762-768	1.6	7

100	Investigation of Self-Heating Effect on DC and RF Performances in AlGa _N /Ga _N HEMTs on CVD-Diamond. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 7, 1264-1269	2.3	7
99	Temperature-Dependent Microwave Noise Characteristics in Al ₂ O ₃ /AlGa _N /Ga _N MISHEMTs on Silicon Substrate. <i>IEEE Electron Device Letters</i> , 2011 , 32, 318-320	4.4	6
98	Comprehensive Study on the Bias-Dependent Equivalent-Circuit Elements Affected by PECVD SiN Passivation in AlGa _N /Ga _N HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 473-479	2.9	6
97	Electrothermal large-signal model of III ^V FETs accounting for frequency dispersion and charge conservation 2009 ,		6
96	Mechanism of Increased High-Frequency Channel Noise With PECVD SiN Passivation in AlGa _N /Ga _N HEMTs. <i>IEEE Electron Device Letters</i> , 2009 , 30, 1122-1124	4.4	6
95	Band gap narrowing effect in Be-doped Al _x Ga _{1-x} As studied by photoluminescence spectroscopy. <i>Solid-State Electronics</i> , 2000 , 44, 37-40	1.7	6
94	Nondestructive determination of sheet carrier density in pseudomorphic AlGaAs/InGaAs/GaAs high electron mobility transistor structures by room-temperature photoluminescence spectra. <i>Journal Physics D: Applied Physics</i> , 1998 , 31, 159-164	3	6
93	A comprehensive study of AlGaAs/GaAs beryllium- and carbon-doped base heterojunction bipolar transistor structures subjected to rapid thermal processing. <i>Journal of Applied Physics</i> , 1999 , 86, 6468-6473	2.5	6
92	New generation MMIC amplifier using InGaAs/InAlAs HEMTs. <i>Electronics Letters</i> , 1990 , 26, 264	1.1	6
91	Low Voltage High-Energy Particle Detectors by GaN-on-GaN Schottky Diodes with Record-High Charge Collection Efficiency. <i>Sensors</i> , 2019 , 19,	3.8	6
90	Low k-dielectric benzocyclobutane encapsulated AlGa _N /Ga _N HEMTs with Improved off-state breakdown voltage. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 036504	1.4	5
89	High temperature characteristics of a 2 μm InGaSb/AlGaAsSb passively mode-locked quantum well laser. <i>Applied Physics Letters</i> , 2019 , 114, 221104	3.4	5
88	Compact microring resonators integrated with grating couplers working at 2 μm wavelength on silicon-on-insulator platform. <i>Applied Optics</i> , 2017 , 56, 5444-5449	0.2	5
87	Kinetics of non-radiative-defect-related degradation in GaAs/AlGaAs heterojunction bipolar transistors. <i>Journal Physics D: Applied Physics</i> , 1998 , 31, 3168-3171	3	5
86	0.25-μm gate In _{0.48} Ga _{0.52} P/In _{0.20} Ga _{0.80} As/GaAs pseudomorphic high electron mobility transistors grown by solid-source molecular beam epitaxy. <i>Solid-State Electronics</i> , 1999 , 43, 785-789	1.7	5
85			5
84	. <i>IEEE Electron Device Letters</i> , 1994 , 15, 380-382	4.4	5
83	InAlAs/InGaAs/InP sub-micron HEMTs grown by CBE. <i>Journal of Crystal Growth</i> , 1992 , 120, 184-188	1.6	5

82	(Invited) Novel Integrated Circuit Platforms Employing Monolithic Silicon CMOS + GaN Devices. <i>ECS Transactions</i> , 2016 , 75, 31-37	1	5
81	Temperature Dependent Characteristics of InAlN/GaN HEMTs for mm-Wave Applications. <i>Procedia Engineering</i> , 2016 , 141, 103-107		5
80	Investigations of temperature-dependent interface traps in AlGaIn/GaN HEMT on CVD-diamond. <i>Applied Physics Express</i> , 2019 , 12, 106506	2.4	4
79	On the recovery of 2DEG properties in vertically ordered h-BN deposited AlGaIn/GaN heterostructures on Si substrate. <i>Applied Physics Express</i> , 2020 , 13, 065508	2.4	4
78	Study on GaN buffer leakage current in AlGaIn/GaN high electron mobility transistor structures grown by ammonia-molecular beam epitaxy on 100-mm Si(111). <i>Journal of Applied Physics</i> , 2015 , 117, 245305	2.5	4
77	Single-step fabrication of surface relief diffractive optical elements on hybrid sol-gel glass. <i>Optical Engineering</i> , 2001 , 40, 2017	1.1	4
76	Design and analysis of coplanar Lange coupler for millimetre-wave applications up to 90 GHz		4
75	Molecular Beam Epitaxial Growth of InP Using a Valved Phosphorus Cracker Cell: Optimization of Electrical, Optical and Surface Morphology Characteristics. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, 981-984	1.4	4
74	Hot-carrier induced degradation in InP/InGaAs/InP double heterojunction bipolar transistors		4
73	MMIC-based W-band Dicke switched direct-detection receiver		4
72	. <i>IEEE Transactions on Electron Devices</i> , 1994 , 41, 1489-1497	2.9	4
71	Vertical GaN-on-GaN Schottky Diodes as Particle Radiation Sensors. <i>Micromachines</i> , 2020 , 11,	3.3	4
70	Improved breakdown voltage in vertical GaN Schottky barrier diodes on free-standing GaN with Mg-compensated drift layer. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, 010906	1.4	4
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68	Experimental Demonstration of Thermally Tunable Fano and EIT Resonances in Coupled Resonant System on SOI Platform. <i>IEEE Photonics Journal</i> , 2018 , 10, 1-8	1.8	4
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